Yukihiro Shimogaki

List of Publications by Year
in descending order

245	2,662	279798	361022
papers	citations	23 h-index	35 g-index

250	250	250	1464
all docs	docs citations	times ranked	citing authors

#	Article	IF	Citations
1	Cu Wettability and Diffusion Barrier Property of Ru Thin Film for Cu Metallization. Journal of the Electrochemical Society, 2005, 152, G594.	2.9	137
2	Chemical reaction engineering in the design of CVD reactors. Chemical Engineering Science, 1999, 54, 1941-1957.	3.8	64
3	Preparation of Low-Dielectric-Constant F-DopedSiO2Films by Plasma-Enhanced Chemical Vapor Deposition. Japanese Journal of Applied Physics, 1996, 35, 1468-1473.	1.5	59
4	Conformal Deposition and Gap-Filling of Copper into Ultranarrow Patterns by Supercritical Fluid Deposition. Applied Physics Express, 0, 1, 097002.	2.4	51
5	Surface Reaction Kinetics in Metalorganic Vapor Phase Epitaxy of GaAs through Analyses of Growth Rate Profile in Wide-Gap Selective-Area Growth. Japanese Journal of Applied Physics, 2003, 42, 6284-6291.	1.5	48
6	Hot-wire-assisted atomic layer deposition of a high quality cobalt film using cobaltocene: Elementary reaction analysis on NHx radical formation. Journal of Vacuum Science and Technology A: Vacuum, Surfaces and Films, 2012, 30, .	2.1	46
7	Reduction Mechanism in the Dielectric Constant of Fluorineâ€Doped Silicon Dioxide Film. Journal of the Electrochemical Society, 1997, 144, 2531-2537.	2.9	44
8	X-ray photoelectron spectroscopic characterization of the adhesion behavior of chemical vapor deposited copper films. Journal of Vacuum Science and Technology A: Vacuum, Surfaces and Films, 2001, 19, 2642-2651.	2.1	43
9	Shortest intersubband transition wavelength (1.68 Î¼m) achieved in AlN/GaN multiple quantum wells by metalorganic vapor phase epitaxy. Applied Physics Letters, 2003, 82, 4465-4467.	3.3	42
10	CVD of cobaltâ€“tungsten alloy film as a novel copper diffusion barrier. Microelectronic Engineering, 2013, 106, 91-95.	2.4	38
11	Material Consideration on Ta, Mo, Ru, and Os as Glue Layer for Ultra Large Scale Integration Cu Interconnects. Japanese Journal of Applied Physics, 2006, 45, 2497-2501.	1.5	37
12	Changes in Orientational Polarization and Structure of Silicon Dioxide Film by Fluorine Addition. Journal of the Electrochemical Society, 1999, 146, 4196-4202.	2.9	36
13	Diffusion barrier property of TiN and TiN/Al/TiN films deposited with FMCVD for Cu interconnection in ULSI. Science and Technology of Advanced Materials, 2004, 5, 399-405.	6.1	36
14	Fundamental kinetics determining growth rate profiles of InP and GaAs in MOCVD with horizontal reactor. Journal of Crystal Growth, 2004, 261, 214-224.	1.5	35
15	Preparation of low dielectric constant Fâ€doped SiO2 films by plasma enhanced chemical vapor deposition. Applied Physics Letters, 1996, 68, 832-834.	3.3	33
16	Macro/microcavity method and its application in modeling chemical vapor deposition reaction systems. Thin Solid Films, 2000, 365, 176-188.	1.8	33
17	Precursor Evaluation for Cu-Supercritical Fluid Deposition Based on Adhesion Properties and Surface Morphology. Japanese Journal of Applied Physics, 2005, 44, L1199-L1202.	1.5	32
18	Kinetics of Deposition of Cu Thin Films in Supercritical Carbon Dioxide Solutions from a F-Free Copper(II) Î²-Diketone Complex. Journal of the Electrochemical Society, 2009, 156, H443.	2.9	32

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19	Atomic Layer Deposited Co(W) Film as a Single-Layered Barrier/Liner for Next-Generation Cu-Interconnects. Japanese Journal of Applied Physics, 2012, 51, 05EB02.	1.5	31
20	The Role of Gasâ€Phase Reactions during Chemical Vapor Deposition of Copper from (hfac)Cu(tmvs). Journal of the Electrochemical Society, 1998, 145, 4226-4233.	2.9	29
21	Comparative Study of Cuâ€“CVD Seed Layer Deposition on Ru and Ta Underlayers. Journal of the Electrochemical Society, 2007, 154, G13.	2.9	29
22	Study of the Reaction of Si2â€‰Hâ€‰6 in the Presence of â€‰Câ€‰2â€‰Hâ€‰2 in Synthesis of SiC Films by LPCVD Using a Macro/microcavity Method. Journal of the Electrochemical Society, 1992, 139, 3652-3659.	2.9	28
23	In-situ As-P exchange monitoring in metal-organic vapor phase epitaxy of InGaAs/InP heterostructure by spectroscopic and kinetic ellipsometry. Thin Solid Films, 1998, 313-314, 604-608.	1.8	28
24	Atomic Layer Deposited Co(W) Film as a Single-Layered Barrier/Liner for Next-Generation Cu-Interconnects. Japanese Journal of Applied Physics, 2012, 51, 05EB02.	1.5	26
25	Effect of Ru crystal orientation on the adhesion characteristics of Cu for ultra-large scale integration interconnects. Applied Surface Science, 2006, 252, 3938-3942.	6.1	24
26	POROUS AND AMORPHOUS Ni67Zr33CATALYST PREPARED BY HYDROGENATION OF CARBON MONOXIDE. Chemistry Letters, 1985, 14, 661-664.	1.3	23
27	Impurity-free Disordering of InGaAs/InGaAlAs Quantum Wells on InP by Dielectric Thin Cap Films and Characterization of Its In-plane Spatial Resolution. Japanese Journal of Applied Physics, 1996, 35, 1276-1279.	1.5	23
28	Polycrystals growth on dielectric masks during InP/GaAs selective MOVPE. Journal of Crystal Growth, 2004, 261, 411-418.	1.5	23
29	Deposition of Cu-Ag Alloy Film by Supercritical Fluid Deposition. Japanese Journal of Applied Physics, 2006, 45, L1296-L1299.	1.5	23
30	Selective Area Metalâ€“Organic Vapor Phase Epitaxy of Nitride Semiconductors for Multicolor Emission. IEEE Journal of Selected Topics in Quantum Electronics, 2009, 15, 1053-1065.	2.9	22
31	A numerical study on heat transfer and film growth rate of InP and GaAs MOCVD process. Journal of Crystal Growth, 2005, 276, 431-438.	1.5	21
32	Influence of Crystal Orientation of Ru Under-Layer on Initial Growth of Copper Chemical Vapor Deposition. Japanese Journal of Applied Physics, 2006, 45, L233-L235.	1.5	21
33	Nonlinear Kinetics of GaAs MOVPE Examined by Selective Area Growth Technique. Journal of the Electrochemical Society, 2007, 154, H91.	2.9	21
34	Acetone-assisted deposition of silver films in supercritical carbon dioxide. Microelectronic Engineering, 2008, 85, 675-681.	2.4	21
35	In situObservation of Initial Nucleation and Growth Processes in Supercritical Fluid Deposition of Copper. Japanese Journal of Applied Physics, 2008, 47, 885-890.	1.5	21
36	Kinetic study on hot-wire-assisted atomic layer deposition of nickel thin films. Journal of Vacuum Science and Technology A: Vacuum, Surfaces and Films, 2014, 32, 01A104.	2.1	21

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37	Electron Cyclotron Resonance-Reactive Ion Beam Etching of InP by Cyclic Injection of CH4/H2/Ar and O2. Japanese Journal of Applied Physics, 2002, 41, 15-19.	1.5	19
38	Interface structure of HfNx/SiO2 stack grown by MOCVD using TDEAHf precursor. Surface Science, 2005, 588, 108-116.	1.9	19
39	Effects of Ag Addition on the Resistivity, Texture and Surface Morphology of Cu Metallization. Japanese Journal of Applied Physics, 2005, 44, L1278-L1281.	1.5	19
40	Blueshift of intersubband transition wavelength in AlN/GaN multiple quantum wells by low temperature metal organic vapor phase epitaxy using pulse injection method. Applied Physics Letters, 2009, 95, .	3.3	19
41	Step Coverage Quality of Cu Films by Supercritical Fluid Deposition Compared with Chemical Vapor Deposition. Japanese Journal of Applied Physics, 2010, 49, 05FF01.	1.5	19
42	Kinetic ellipsometry measurement of InGaP/GaAs hetero-interface formation in MOVPE. Journal of Crystal Growth, 2000, 221, 136-141.	1.5	18
43	Nucleation of W during Chemical Vapor Deposition from WF6and SiH4. Japanese Journal of Applied Physics, 2004, 43, 3945-3950.	1.5	18
44	The effect of group V precursor on selective area MOVPE of InP/GaAs-related materials. Journal of Crystal Growth, 2004, 261, 419-426.	1.5	18
45	Simulation and design of the emission wavelength of multiple quantum well structures fabricated by selective area metalorganic chemical vapor deposition. Thin Solid Films, 2006, 498, 174-178.	1.8	18
46	Multi-Scale Analysis and Elementary Reaction Simulation of SiC-CVD Using CH₃SiCl₃/H₂. ECS Journal of Solid State Science and Technology, 2013, 2, P492-P497.	1.8	18
47	TiN Films Prepared by Flow Modulation Chemical Vapor Deposition using TiCl4and NH3. Japanese Journal of Applied Physics, 2001, 40, 1517-1521.	1.5	17
48	Process design of Cu(Sn) alloy deposition for highly reliable ultra large-scale integration interconnects. Thin Solid Films, 2005, 491, 221-227.	1.8	17
49	Effect of liquid additives in supercritical fluid deposition of copper for enhancing deposition chemistry. Thin Solid Films, 2008, 517, 674-680.	1.8	17
50	Abrupt InGaPâˆ•GaAs heterointerface grown by optimized gas-switching sequence in metal organic vapor phase epitaxy. Applied Physics Letters, 2008, 92, 112106.	3.3	17
51	In situ passivation of InP surface using H2S during metal organic vapor phase epitaxy. Applied Physics Letters, 2009, 95, 152103.	3.3	17
52	Selective area metal-organic vapor-phase epitaxy of InN, GaN and InGaN covering whole composition range. Journal of Crystal Growth, 2009, 311, 2809-2812.	1.5	17
53	Particle Generation on Hydrogen-Terminated Si Surface by Brush Scrubbing of Polyvinyl Alcohol. Journal of the Electrochemical Society, 2011, 158, D651.	2.9	17
54	Role of NH3 feeding period to realize high-quality nickel films by hot-wire-assisted atomic layer deposition. Microelectronic Engineering, 2014, 120, 230-234.	2.4	16

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55	Effect of Surface Misorientation on the Kinetics of GaAs MOVPE Examined Using Selective Area Growth. Electrochemical and Solid-State Letters, 2006, 9, G104.	2.2	15
56	High-resolution transmission electron microscopy (HRTEM) observation of dislocation structures in AlN thin films. Journal of Materials Research, 2008, 23, 2188-2194.	2.6	15
57	Analysis of the Gas Phase Kinetics Active during GaN Deposition from NH₃ and Ga(CH₃)₃. Journal of Physical Chemistry A, 2015, 119, 7858-7871.	2.5	15
58	PREPARATION OF AMORPHOUS TiO2FILMS BY THERMOPHORESIS-AIDED CHEMICAL VAPOR DEPOSITION. Chemistry Letters, 1986, 15, 267-268.	1.3	14
59	Conformal deposition of WSixfilms on micronâ€sized trenches: The reactivity of film precursors. Applied Physics Letters, 1992, 61, 764-765.	3.3	14
60	Stepâ€Coverage Simulation for Tetraethoxysilane and Ozone Atmospheric Pressure Chemical Vapor Deposition. Journal of the Electrochemical Society, 1993, 140, 2309-2312.	2.9	14
61	Chemical Vapor Deposition Reactor Design Using Smallâ€Scale Diagnostic Experiments Combined with Computational Fluid Dynamics Simulations. Journal of the Electrochemical Society, 1999, 146, 1780-1788.	2.9	14
62	Kinetics of GaAs Metalorganic Chemical Vapor Deposition Studied by Numerical Analysis Based on Experimental Reaction Data. Japanese Journal of Applied Physics, 2000, 39, 1642-1649.	1.5	14
63	Comparison of Organic and Hydride Group V Precursors in Terms of Surface Kinetics in Wide-Gap Selective Area Metalorganic Vapor Phase Epitaxy. Japanese Journal of Applied Physics, 2003, 42, L1195-L1197.	1.5	14
64	Control of abnormal edge growth in selective area MOVPE of InP. Journal of Crystal Growth, 2006, 287, 668-672.	1.5	14
65	Vapor phase diffusion and surface diffusion combined model for InGaAsP selective area metalâ€“organic vapor phase epitaxy. Journal of Crystal Growth, 2007, 298, 37-40.	1.5	14
66	CVD and ALD Co(W) Films Using Amidinato Precursors as a Single-Layered Barrier/Liner for Next-Generation Cu-Interconnects. ECS Journal of Solid State Science and Technology, 2013, 2, P311-P315.	1.8	14
67	Precursor-based designs of nano-structures and their processing for Co(W) alloy films as a single layered barrier/liner layer in future Cu-interconnect. Journal of Materials Chemistry C, 2015, 3, 2500-2510.	5.5	14
68	Deposition ofWSixFilms from Preactivated Mixture ofWF6/SiH4. Japanese Journal of Applied Physics, 1994, 33, 275-279.	1.5	13
69	Kinetic study of P and As desorption from binary and ternary IIIâ€“V semiconductors surface by in situ ellipsometry. Journal of Crystal Growth, 2000, 221, 129-135.	1.5	13
70	The Fabrication of Hafnium Nitride by Metal Organic Chemical Vapor Deposition (MOCVD) Using TDEAHf Precursor for Gate-Electrode Application. Japanese Journal of Applied Physics, 2004, 43, L1445-L1448.	1.5	13
71	Chemical Vapor Deposition of TiAlN film by Using Titanium Tetrachloride, Dimethylethylamine Alane and Ammonia Gas for ULSI Cu Diffusion Barrier Application. Japanese Journal of Applied Physics, 2004, 43, 8253-8257.	1.5	13
72	Effect of group V partial pressure on the kinetics of selective area MOVPE for GaAs on (100) exact and misoriented substrate. Journal of Crystal Growth, 2006, 287, 664-667.	1.5	13

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73	Preparation of conductive HfN by post rapid thermal annealing-assisted MOCVD and its application to metal gate electrode. Microelectronic Engineering, 2008, 85, 320-326.	2.4	13
74	Elementary Surface Reaction Simulation of Aluminum Chemical Vapor Deposition from Dimethylaluminumhydride Based onAb InitioCalculations: Theoretical Process Optimization Procedure (2). Japanese Journal of Applied Physics, 2000, 39, 6501-6512.	1.5	12
75	Fabrication of Hf(C)N Films on SiO2by Metal Organic Chemical Vapor Deposition (MOCVD) Using TDEAHf Precursor. Japanese Journal of Applied Physics, 2005, 44, L348-L351.	1.5	12
76	Effect of NH3 on the fabrication of HfN as gate-electrode using MOCVD. Thin Solid Films, 2006, 498, 75-79.	1.8	12
77	Low Temperature Metal Organic Vapor Phase Epitaxial Growth of AlN by Pulse Injection Method at 800 Â°C. Japanese Journal of Applied Physics, 2007, 46, L927-L929.	1.5	12
78	Kinetic Analysis of InN Selective Area Metalâ€“Organic Vapor Phase Epitaxy. Applied Physics Express, 2008, 1, 071102.	2.4	12
79	Chemical Bonding States and Band Alignment of Ultrathin AlO_xN_y/Si Gate Stacks Grown by Metalorganic Chemical Vapor Deposition. Applied Physics Express, 0, 2, 075503.	2.4	12
80	Strain effects on the intersubband transitions in GaN/AlN multiple quantum wells grown by low-temperature metal organic vapor phase epitaxy with AlGaN interlayer. Applied Physics Letters, 2009, 95, .	3.3	12
81	Multiscale Analysis of Silicon Carbide-Chemical Vapor Deposition Process. Journal of Nanoscience and Nanotechnology, 2011, 11, 7988-7993.	0.9	12
82	Strontium ruthenium oxide deposition in supercritical carbon dioxide using a closed reactor system. Journal of Supercritical Fluids, 2013, 79, 244-250.	3.2	12
83	Development of TiSiN CVD process using TiCl4/SiH4/NH3chemistry for ULSI anti-oxidation barrier applications. Science and Technology of Advanced Materials, 2004, 5, 549-554.	6.1	11
84	Ultra-Conformal Metal Coating on High-Aspect-Ratio Three-Dimensional Structures Using Supercritical Fluid: Controlled Selectivity/Non-Selectivity. Japanese Journal of Applied Physics, 2012, 51, 056502.	1.5	11
85	Smooth and Conformal TiO₂Thin-Film Formation Using Supercritical Fluid Deposition. ECS Journal of Solid State Science and Technology, 2013, 2, N191-N195.	1.8	11
86	Physical and Chemical Contributions of Interfacial Impurities to Film Adhesion. Japanese Journal of Applied Physics, 2001, 40, L1380-L1383.	1.5	10
87	Investigation on GaAs surface treated with dimethylaluminumhydride. Applied Physics Letters, 2009, 95, .	3.3	10
88	Process design of the pulse injection method for low-temperature metal organic vapor phase epitaxial growth of AlN at 800Â°C. Journal of Crystal Growth, 2009, 311, 383-388.	1.5	10
89	Impacts of Chemical Supply Flow on Particle Removability in Wet Clean Bath. Journal of the Electrochemical Society, 2012, 159, H367-H372.	2.9	10
90	Ultra-Conformal Metal Coating on High-Aspect-Ratio Three-Dimensional Structures Using Supercritical Fluid: Controlled Selectivity/Non-Selectivity. Japanese Journal of Applied Physics, 2012, 51, 056502.	1.5	10

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91	Activation mechanism of amorphous NixZr100-x alloys during CO/H2 reaction and preparation method of porous amorphous alloy catalysts.. Journal of Chemical Engineering of Japan, 1988, 21, 293-299.	0.6	9
92	Structural change of TiN/Ti/SiO2 multilayers by N2 annealing. Thin Solid Films, 1998, 320, 31-34.	1.8	9
93	Reaction Analysis of Aluminum Chemical Vapor Deposition from Dimethyl-aluminum-hydride Using Tubular Reactor and Fourier-Transform Infrared Spectroscopy: Theoretical Process Optimization Procedure (1). Japanese Journal of Applied Physics, 2000, 39, 1074-1079.	1.5	9
94	Adhesion Characteristics between Chemical Vapor Deposited Cu and TiN Films: Aspects of Process Integration. Japanese Journal of Applied Physics, 2002, 41, 1500-1506.	1.5	9
95	Factors Determining the Generation of Polycrystalline Growth over Masks in Selective-Area Metalorganic Vapor Phase Epitaxy: Gas-Phase Concentration Analysis. Japanese Journal of Applied Physics, 2003, 42, L359-L361.	1.5	9
96	The role of the surface adsorption layer during MOVPE growth analyzed by the flow modulation method. Journal of Crystal Growth, 2004, 272, 15-23.	1.5	9
97	Non-linear kinetic analysis on GaAs selective area MOVPE combined with macro-scale analysis to extract major reaction mechanism. Journal of Crystal Growth, 2007, 298, 32-36.	1.5	9
98	Intersubband Transition at 1.52 Âμm in GaN/AlN Multiple Quantum Wells Grown by Metal Organic Vapor Phase Epitaxy. Applied Physics Express, 0, 2, 061002.	2.4	9
99	Fabrication of Abrupt AlN/GaN Multi Quantum Wells by Low Temperature Metal Organic Vapor Phase Epitaxy. Applied Physics Express, 0, 2, 051004.	2.4	9
100	Initial Cu Growth in Cu-Seeded and Ru-Lined Narrow Trenches for Supercritical Fluid Cu Chemical Deposition. Japanese Journal of Applied Physics, 2010, 49, 05FA07.	1.5	9
101	Self-Assembled Nano-Stuffing Structure in CVD and ALD Co(W) Films as a Single-Layered Barrier/Liner for Future Cu-Interconnects. ECS Journal of Solid State Science and Technology, 2013, 2, P471-P477.	1.8	9
102	Novel gas-switching sequence using group-III pre-flow (GIIIP) method for fabrication of InGaP on GaAs hetero-interface by MOVPE. Journal of Crystal Growth, 2006, 296, 179-185.	1.5	8
103	Intersubband absorption saturation in AlN-based waveguide with GaN/AlN multiple quantum wells grown by metalorganic vapor phase epitaxy. Applied Physics Letters, 2011, 99, 151102.	3.3	8
104	Role of W and Mn for reliable 1X nanometer-node ultra-large-scale integration Cu interconnects proved by atom probe tomography. Applied Physics Letters, 2014, 105, 133512.	3.3	8
105	Experimental and numerical analysis of rapid reaction to initiate the radical chain reactions in WSix CVD. Thin Solid Films, 1998, 320, 151-158.	1.8	7
106	Effect of Underlayers on the Morphology and Orientation of Aluminum Films Prepared by Chemical Vapor Deposition Using Dimethylaluminumhydride. Japanese Journal of Applied Physics, 1999, 38, L1528-L1531.	1.5	7
107	Decrease in Deposition Rate and Improvement of Step Coverage by CF4Addition to Plasma-Enhanced Chemical Vapor Deposition of Silicon Oxide Films. Japanese Journal of Applied Physics, 2000, 39, 330-336.	1.5	7
108	Kinetics of TiN Chemical Vapor Deposition Process using TiCl4and NH3for ULSI Diffusion Barrier Applications: Relationship between Step Coverage and NH3Partial Pressure. Japanese Journal of Applied Physics, 2004, 43, 7287-7291.	1.5	7

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109	Electrical and Thermal Stability Characteristics of HfCN Films as Metal Gate-Electrode Synthesized by Metalorganic Chemical Vapor Deposition. Japanese Journal of Applied Physics, 2005, 44, L1019-L1021.	1.5	7
110	GaN Selective Area Metalâ€“Organic Vapor Phase Epitaxy: Prediction of Growth Rate Enhancement by Vapor Phase Diffusion Model. Japanese Journal of Applied Physics, 2007, 46, L1045.	1.5	7
111	Kinetic modeling of tungsten silicide chemical vapor deposition from WF6 and Si2H6: Determination of the reaction scheme and the gas-phase reaction rates. Chemical Engineering Science, 2007, 62, 6403-6411.	3.8	7
112	Kinetics of Subsurface Formation during Metalâ€“Organic Vapor Phase Epitaxy Growth of InP and InGaP. Japanese Journal of Applied Physics, 2008, 47, 1473-1478.	1.5	7
113	Evaluation of a novel unfluorinated copper precursor for chemical vapor deposition. Microelectronic Engineering, 2010, 87, 249-253.	2.4	7
114	Selectivity enhancement by hydrogen addition in selective area metalâ€•organic vapor phase epitaxy of GaN and InGaN. Physica Status Solidi (A) Applications and Materials Science, 2010, 207, 1375-1378.	1.8	7
115	Isobutyl Silane Precursors for SiCH Low-kCap Layer beyond the 22 nm Node: Analysis of Film Structure for Compatibility of Lowerk-value and High Barrier Properties. Japanese Journal of Applied Physics, 2011, 50, 05EB01.	1.5	7
116	A 50 nm-wide 5 μm-deep copper vertical gap formation method by a gap-narrowing post-process with Supercritical Fluid Deposition for Pirani gauge operating over atmospheric pressure. , 2012, , .		7
117	Potential Step Coverage for Supercritical Fluid Deposition of TiO2 by Numerical Simulation and Microcavity Analysis. ECS Solid State Letters, 2013, 2, P79-P81.	1.4	7
118	Separate evaluation of multiple film-forming species in chemical vapor deposition of SiC using high aspect-ratio microchannels. Japanese Journal of Applied Physics, 2017, 56, 06HE02.	1.5	7
119	Fundamental Evaluation of Gas-Phase Elementary Reaction Models for Silicon Carbide Chemical Vapor Deposition. ECS Journal of Solid State Science and Technology, 2017, 6, P399-P404.	1.8	7
120	Conformal and Stoichiometric Chemical Vapor Deposition of Silicon Carbide onto Ultradeep Heterogeneous Micropores by Controlling the Initial Nucleation Stage. ACS Applied Materials & Interfaces, 2021, 13, 53009-53020.	8.0	7
121	Composition change of SiCx(x=1â€“2) films due to variation of film precursors in the Si2H6/C2H2chemical vapor deposition reaction system. Applied Physics Letters, 1992, 61, 910-912.	3.3	6
122	Electron Cyclotron Resonance-Reactive Ion Etching of III-V Semiconductors by Cyclic Injection of CH4/H2/Ar and O2with Constant Ar Flow. Japanese Journal of Applied Physics, 2003, 42, 3958-3961.	1.5	6
123	Stranskiâ€“Krastanov Growth of Tungsten during Chemical Vapor Deposition Revealed by Micro-Auger Electron Spectroscopy. Japanese Journal of Applied Physics, 2004, 43, 6974-6977.	1.5	6
124	Optimization of Al-CVD process based on elementary reaction simulation and experimental verification: From the growth rate to the surface morphology. Thin Solid Films, 2006, 498, 30-35.	1.8	6
125	In SituObservation of Initial Nucleation and Growth of Chemical Vapor Deposition of Copper by Surface Reflectivity Measurement. Japanese Journal of Applied Physics, 2006, 45, 8618-8623.	1.5	6
126	High Temperature Annealing-Induced Phase Transformation Characteristic of Nitrogen-Rich Hafnium Nitride Films. Japanese Journal of Applied Physics, 2006, 45, L1183-L1185.	1.5	6

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127	Thermal stability and chemical bonding states of AlO N /Si gate stacks revealed by synchrotron radiation photoemission spectroscopy. Applied Surface Science, 2010, 257, 1638-1642.	6.1	6
128	Metalorganic Chemical Vapor Deposition of Al2O3Thin Films from Dimethylaluminumhydride and O2. Japanese Journal of Applied Physics, 2010, 49, 031502.	1.5	6
129	Novel Precursors for SiCH Low-k Caps beyond the 22 nm Node: Reactions of Silacyclopentane Precursors in the Plasma-Enhanced Chemical Vapor Deposition Process and Structural Analyses of SiCH Films. Japanese Journal of Applied Physics, 2011, 50, 08KA01.	1.5	6
130	Study on the Adhesion Strength of CVD-Cu Films with CVD/ALD-Co(W) Underlayers Made Using Carbonyl Precursors. ECS Solid State Letters, 2013, 3, P20-P22.	1.4	6
131	Solubility of bis-(2,2,6,6-tetramethyl-3,5-heptanedionato)copper(II) in mixed supercritical CO2 and H2 systems for application in supercritical fluid deposition of Cu. Journal of Supercritical Fluids, 2015, 105, 193-200.	3.2	6
132	Highâ€Aspectâ€Ratio Parallelâ€Plate Microchannels Applicable to Kinetic Analysis of Chemical Vapor Deposition. Advanced Materials Interfaces, 2016, 3, 1600254.	3.7	6
133	Modeling of the elementary gasâ€phase reaction during chemical vapor deposition of silicon carbide from CH₃SiCl₃/H₂. International Journal of Chemical Kinetics, 2020, 52, 359-367.	1.6	6
134	Design of a Multi-Wafer Reactor for Supercritical Fluid Deposition of Cu in Mass Production: (1) Reaction Mechanism and Kinetics. Journal of Chemical Engineering of Japan, 2014, 47, 737-742.	0.6	6
135	Role of surface diffusion during selective area MOVPE growth of InP. Thin Solid Films, 2006, 498, 163-166.	1.8	5
136	Thin and Smooth Cu Seed Layer Deposition using the Reduction of Low Temperature Deposited Cu₂O. Materials Research Society Symposia Proceedings, 2006, 914, 1.	0.1	5
137	High-resolution depth profile of the InGaP-on-GaAs heterointerface by FE-AES and its relationship to device properties. Journal of Crystal Growth, 2007, 298, 85-89.	1.5	5
138	Competitive Kinetics Model to Explain Surface Segregation of Indium during InGaP Growth by Using Metal Organic Vapor Phase Epitaxy. Japanese Journal of Applied Physics, 2009, 48, 011101.	1.5	5
139	Role of vapor-phase diffusion in selective-area MOVPE of InGaN/GaN MQWs. Journal of Crystal Growth, 2009, 311, 2813-2816.	1.5	5
140	Pattern Density Dependency of the Underlying Layer on O₃-Tetraethylorthosilicate (TEOS) Film Formation. ECS Journal of Solid State Science and Technology, 2012, 1, N91-N96.	1.8	5
141	Ethanol-Assisted Flow-Type Supercritical Fluid Deposition of SrRuO3 for Stoichiometric Film Formation. ECS Solid State Letters, 2013, 2, P70-P72.	1.4	5
142	Material design of plasma-enhanced chemical vapour deposition SiCH films for low-kcap layers in the further scaling of ultra-large-scale integrated devices-Cu interconnects. Science and Technology of Advanced Materials, 2013, 14, 055005.	6.1	5
143	Kinetic study of alcohol-assisted supercritical fluid deposition of TiO2. Thin Solid Films, 2014, 553, 184-187.	1.8	5
144	Study on the Adhesion Strength of CVD-Cu Films with ALD-Co(W) Underlayers Made Using Amidinato Precursors. ECS Journal of Solid State Science and Technology, 2015, 4, P20-P29.	1.8	5

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145	Comparative Study on Cu-CVD Nucleation Using Î²-diketonato and Amidinato Precursors for Sub-10-nm-Thick Continuous Film Growth. ECS Journal of Solid State Science and Technology, 2015, 4, P305-P313.	1.8	5
146	Conformal Bismuth Titanate Formation Using Supercritical Fluid Deposition. ECS Journal of Solid State Science and Technology, 2017, 6, P483-P488.	1.8	5
147	Identification of Film-Forming Species during SiC-CVD of CH₃SiCl₃/H₂ by Exploiting Deep Microtrenches. ECS Journal of Solid State Science and Technology, 2019, 8, P423-P429.	1.8	5
148	Elementary gasâ€phase reactions of radical species during chemical vapor deposition of silicon carbide using CH 3 SiCl 3. International Journal of Chemical Kinetics, 2021, 53, 638-645.	1.6	5
149	Development of a model for evaluating propagation loss of metal-coated dielectric terahertz waveguides. Journal of Applied Physics, 2021, 130, .	2.5	5
150	Design of a Multi-Wafer Reactor for Supercritical Fluid Deposition of Cu in Mass Production: (2) Benchmarks for Single- and Multiple-Wafer Reactors. Journal of Chemical Engineering of Japan, 2014, 47, 743-749.	0.6	5
151	Step Coverage Analysis for Hexamethyldisiloxane and Ozone Atmospheric Pressure Chemical Vapor Deposition. Japanese Journal of Applied Physics, 1994, 33, L473-L475.	1.5	4
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